

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Huilong ZHU et al.

Confirmation No.: 1839

Serial No: 10/707,840

Group Art Unit: 2811

Filed: January 16, 2004

Examiner: Nguyen, Dao H.

**For: PROTECTING SILICON GERMANIUM SIDEWALL WITH SILICON
FOR STRAINED SILICON/SILICON GERMANIUM MOSFETS**

**COMMUNICATION UNDER 37 C.F.R. §1.312 REQUESTING
CONSIDERATION OF DISCLOSED REFERENCES**

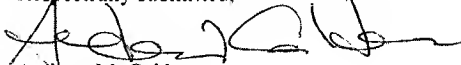
Commissioner for Patents
Customer Service Window, Mail Stop
Randolph Building
401 Dulany Street
Alexandria VA 22314

Sir:

On November 29, 2006, a Notice of Allowance was entered in the above-identified patent application. The issue fee has not been paid. The Notice of Allowance nor another paper acknowledge consideration of the Information Disclosure Statement (IDS) filed on May 9, 2006. Attached hereto for the convenience of the Examiner is the PTO-1449 form filed with the IDS. Applicants request the Examiner note consideration of the references disclosed on the PTO-1449 form by signing and returning the PTO-1449 form to the undersigned representative of Applicant.

No fee is necessary since such oversight was not due to any error by Applicant. The Examiner is invited to contact the undersigned at the telephone number listed below if anything further is needed.

Respectfully submitted,



Andrew M. Calderon

Reg. No. 38,093

Greenblum & Bernstein, P.L.C.
1950 Roland Clarke Place
Reston, Virginia 20191
Telephone: 703-716-1191
Facsimile: 703-716-1180

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27127	Application No. 10/707,840		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Huilong ZHU et al.			
				Filing Date January 16, 2004		Group 2811	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
		JP 64-76755	3-22-1989	Japan			X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. Applicant Filing Date		Application No. Group	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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EXAMINER				DATE CONSIDERED			
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